SILICON NPN SWITCHING TRANSISTOR

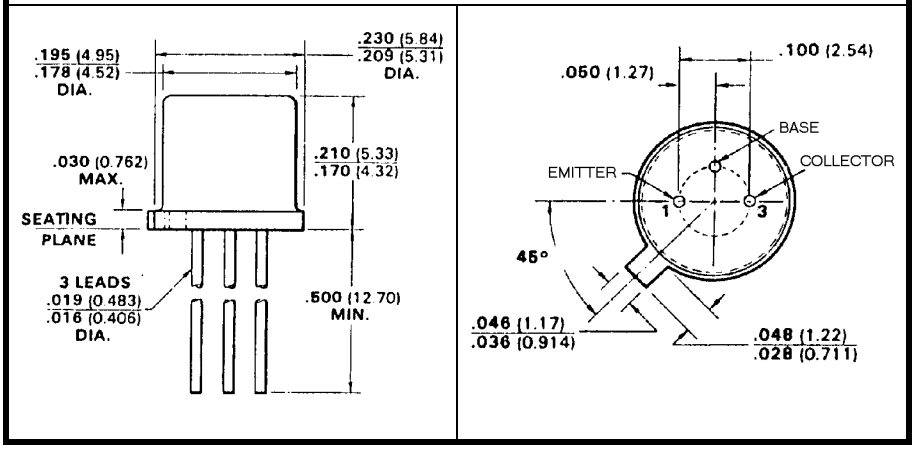
DESCRIPTION:

The **2N2432** is Designed for Low Level High Speed Chopper Applications and is Used Inverted.

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	30 V
P_{DISS}	600 mW @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	291 ^{O}C/W

PACKAGE STYLE TO-18



CHARACTERISTICS T_C= 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 100 µA			30			V
BV_{CE0}	I_C = 10 mA			30			V
BV_{ECO}	I_E = 100 µA			15			
I_{CBO}	V_{CB} = 25 V					10	nA1
I_{EBO}	V_{EB} = 15 V					2.0	nA
I_{CES}	V_{CE} = 25 V	V_{BE} = 0 V				10	nA
			T_A = 125 ^{O}C			250	
I_{ECS}	V_{CE} = 15 V	V_{BC} = 0 V				2.0	nA
			T_A = 125 ^{O}C			200	
h_{FE}	V_{CE} = 5.0 V	I_C = 10 µA		30			---
	V_{CE} = 5.0 V	I_C = 1.0 mA		50			
$h_{FE(INV)}$	V_{CE} = 5.0 V	I_E = 200 µA		2.0			---
$V_{CE(SAT)}$	I_C = 10 mA	I_B = 0.5 mA				0.15	V
$V_{EC(ofs)}$	I_E = 0 A	I_B = 200 µA				0.5	V
$V_{EC(ofs)}$	I_E = 0 A	I_B = 1.0 mA				1.0	V
f_t	V_{CE} = 5.0 V	I_C = 1.0 mA	f = 20 MHz	1.0			---
$r_{ec(on)}$	I_E = 0A	I_B = 1.0 mA	f = 1.0 KHz			20	Ω
C_{ob}	V_{CB} = 0 V		f = 140 KHz			12	pF
C_{ib}	V_{EB} = 0 V		f = 140 KHz			12	pF